Robust Isothermal Electric Control Of Exchange Bias At Room Temperature

Christian Binek[1], Xi He[1], Yi Wang[1], N. Wu[1], A. Wysocki[1], T. Komesu[1], U. Lanke[2], A. N. Caruso[3], E. Vescovo[4], K. D. Belashchenko[1], and P. A. Dowben[1]

[1]Department of Physics & Astronomy and Nebraska Center for Materials and Nanoscience, University of Nebraska, Lincoln, NE, 68588-0111
[2] Canadian Light Source Inc., University of Saskatchewan, Saskatoon, Saskatchewan, Canada S7N 0X4
[3]Department of Physics, 257 Flarsheim Hall, University of Missouri, Kansas City KS 64110
[4]Brookhaven National Laboratory, National Synchrotron Light Source, Upton, NY, 11973

Voltage-controlled spintronics is of particular importance to continue progress in information technology through reduced power consumption, enhanced processing speed, integration density, and functionality in comparison with present day CMOS electronics. Almost all existing and prototypical solid-state spintronic devices rely on tailored interface magnetism, enabling spin-selective transmission or scattering of electrons. Controlling magnetism at thin-film interfaces, preferably by purely electrical means, is a key challenge to better spintronics. Currently, most attempts to electrically control magnetism focus on potentially large magnetoelectric effects of multiferroics. We report on our interest in magnetoelectric Cr_2O_3 (chromia).

Robust isothermal electric control of exchange bias is achieved at room temperature in perpendicular anisotropic Cr_2O_3(0001)/CoPd exchange bias heterostructures.[1] This discovery promises significant implications for potential spintronics. From the perspective of basic science, our finding serves as macroscopic evidence for roughness-insensitive and electrically controllable equilibrium boundary magnetization in magnetoelectric antiferromagnets. Boundary magnetization evolves at surfaces of magnetoelectric antiferromagnets such as Cr_2O_3(0001) and related interfaces when chromia is in one of its two degenerate antiferromagnetic single domain states selected via magnetoelectric annealing. Theoretical insight into the boundary magnetization and its role in electrically controlled exchange bias is gained from first-principles calculations and general symmetry arguments. Measurements of spin-resolved ultraviolet photoemission, magnetometry at Cr_2O_3(0001) surfaces, and detailed investigations of the unique exchange bias properties of Cr_2O_3(0001)/CoPd including its electric controllability provide macroscopically averaged information about the boundary magnetization of chromia. Laterally resolved x-ray PEEM and temperature dependent magnetic force microscopy reveal detailed microscopic information of the chromia (0001) surface magnetization and provide a coherent interpretation of our results on the isothermal electric control of exchange bias.[2] The latter promise a new route towards purely voltage-controlled spintronics and an exciting way to electrically control magnetism.
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[1]Xi He, Yi Wang, Ning Wu, A. N. Caruso, E. Vescovo., K. D. Belashchenko, P. A. Dowben & Ch. Binek, Nature Mater.**9**, 579–585 (2010).
[2]Ning Wu, Xi He, Aleksander L. Wysocki, Uday Lanke, Takashi Komesu, Kirill D. Belashchenko, Christian Binek, and Peter A. Dowben, Phys. Rev. Lett. **106**, 087202 (2011).